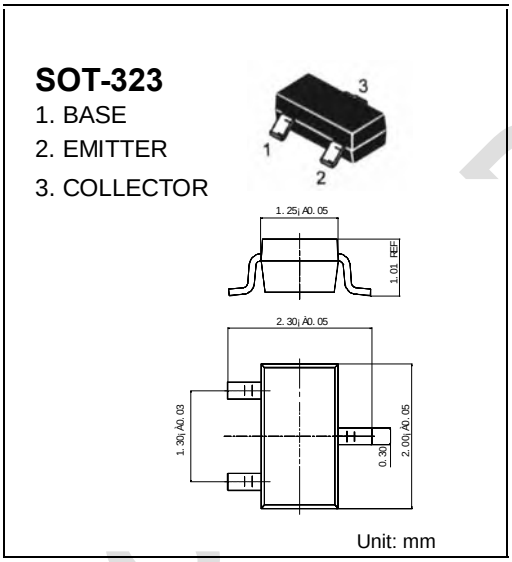
MMST2222A TRANSISTOR (NPN)



FEATURES

Power dissipation

P_{CM}: 0.2 W (Tamb=25℃)

Collector current

I_{CM}: 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 75 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic= 10μA, I_E=0	75		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= 10mA, I_B=0	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=10μA, I_C=0	6		V
Collector cut-off current	I_{CBO}	V_{CB}=70V, I_E=0		0. 1	μA
Collector cut-off current	I_{CEO}	V_{CE}=35V, I_B=0		0. 1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= 3V, I_C=0		0. 1	μA
DC current gain	$h_{FE(1)}$	V_{CE}=10V, I_C= 150mA	100	300	
	$h_{FE(2)}$	V_{CE}=10V, I_C= 1mA	50		
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=500 mA, I_B= 50mA		0.6	V
Base-emitter saturation voltage	V_{BE}(sat)	I_C=500 mA, I_B= 50mA		1.2	V
Transition frequency	f_T	V_{CE}=20V, I_C= 20mA f=100MHz	300		MHz
Output Capacitance	C_{ob}	V_{CB}=10V, I_E= 0 f=1MHz		8	pF
Delay time	t_d	V_{CC}=30V, I_C=150mA		10	nS
Rise time	t_r	$V_{BE(off)}$=0.5V, I_{B1}=15mA		25	nS
Storage time	t_S	V_{CC}=30V, I_C=150mA		225	nS
Fall time	t_f	I_{B1}= I_{B2}= 15mA		60	nS

Marking	**K3P**